

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	5246	(multilayer\$3 or (multi adj layer\$3) or multi-layer\$3) with (gate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/12 13:20
L3	1745	(silicon and germanium) with gate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/12 13:22
L4	307	3 and (multilayer\$3 or (multi adj layer\$3) or multi-layer\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/12 13:21
L5	303	4 and (semiconductor or MOS or transistor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/12 13:22
L6	1148	(silicon adj germanium) with gate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/12 13:22
L7	227	6 and (multilayer\$3 or (multi adj layer\$3) or multi-layer\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/12 13:22
L8	117	6 and ((multilayer\$3 or (multi adj layer\$3) or multi-layer\$3) with gate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/12 13:33
L9	1	("6589827").PN.	USPAT	OR	OFF	2005/04/12 13:33
L10	1224	438/142.ccls. or 438/197.ccls. or 438/199.ccls.	USPAT	OR	ON	2005/04/12 14:01
L11	745	438/585.ccls.	USPAT	OR	ON	2005/04/12 14:01
L12	1516	438/592.ccls. or 438/595.ccls.	USPAT	OR	ON	2005/04/12 14:01
L13	3084	L10 or L11 or L12	USPAT	OR	ON	2005/04/12 14:01

L14	319	13 and (silicon with germanium)	USPAT	OR	ON	2005/04/12 14:01
L15	280	14 and (gate and transistor and semiconductor)	USPAT	OR	ON	2005/04/12 14:02
L16	167	15 and (anneal\$3 and implant\$3)	USPAT	OR	ON	2005/04/12 14:02
L17	164	16 not 8	USPAT	OR	ON	2005/04/12 14:02
S1	1083	(multilayered or multilayer or (multi-layer) or (multi-layered) or (multi adj layered) or (multi adj layer)) with (gate adj electrode)	USPAT	OR	ON	2005/04/12 13:19
S2	30	S1 and ((gate adj electrode) with (silicon and germanium))	USPAT	OR	ON	2005/03/17 17:58
S3	2286	(multilayered or multilayer or (multi-layer) or (multi-layered) or (multi adj layered) or (multi adj layer)) with (gate adj electrode)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/17 17:57
S4	79	S3 and ((gate adj electrode) with (silicon and germanium))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/17 17:58
S5	35	S4 and (p-type with (impurity or impurities))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/17 17:58
S6	24	S5 and anneal\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/17 18:41
S7	1205	438/142.ccls. or 438/197.ccls. or 438/199.ccls.	USPAT	OR	ON	2005/03/17 18:43
S8	737	438/585.ccls.	USPAT	OR	ON	2005/03/17 18:43
S9	1501	438/592.ccls. or 438/595.ccls.	USPAT	OR	ON	2005/03/17 18:43
S10	3046	S7 or S8 or S9	USPAT	OR	ON	2005/04/12 14:01
S11	356	S10 and (silicon and germanium)	USPAT	OR	ON	2005/03/17 18:44
S12	51	S11 and ((gate adj electrode) with (silicon and germanium))	USPAT	OR	ON	2005/03/17 18:44